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List of Contents, Volume 47, 1994

Membrane Oscillations and Ion Transport 1
by S. KIHARA and K. MAEDA

Desorption Induced by Electronic Transitions 55
by V.N. AGEEV

Surface Force Measurements in Surfactant Systems 205
by J.L. PARKER

Fluoropolymer Metallization for Microelectronic Applications 273
by E. SACHER

Inection Spectroscopy of Localized States in Thin 301
Insulating Layers on Semiconductor Surfaces
by V.V. AFANAS'EV and V.K. ADAMCHUK

AUTHOR INDEX

Abatti, P.J. 53
Abillon, O. 271
Abraham, M.Z. 296
Abrams, J.H. 202
Adamchuk, V.K. 389, 390, 391, 392, 393, 394
Adams, G.E. 268
Afanas'ev, V.V. 389, 391, 392, 393
Ageev, V.N. 189, 190, 191, 192, 193, 194, 195, 196, 197, 198, 199, 200
Agnew, J.Reine 269
Aiba, S. 53
Aitken, J.M. 390, 392
Akulov, A.Ph. 394
Albridge, R.G. 193
Alexandrova, S. 389
Alvey, M.D. 193, 195, 198, 199, 200, 203
Amelin, E.A. 270
Andrews, J.M. 389
Andrews, M.P. 300
Ang, S.S. 392
Antoniewicz, P.R. 200
Antonov, V.F. 54
Aoki, Y. 297
Aoyama, H. 54
Appelbaum, J.A. 190
Arai, K. 53
Arakava, I. 198
Araki, T. 54
Arias, J. 198
Arisawa, J. 53
Arlt, G. 390
Arnett, P.C. 394
Arnold, A. 393
Arnold, G.W. 299
Ashcroft, K.W. 191
Aslam, M. 390
Attard, P. 268, 269, 270, 271
Auer, S. 194, 195, 199
Avakian, P. 296
Avouris, P. 297
Avouris, Ph. 193, 194, 195, 197, 199, 200, 201, 202, 203
Ayukhanov, A.Kh. 191
Azakawa, I. 193
Azria, R. 196, 202
Back, W. 192
Baglin, J.E.E. 298, 299
Bakshi, M. 198
Bakshi, M.H. 194
Balasinski, A. 394
Balbuena, P.B. 270
Balk, P. 390
Balland, B. 389
Bange, K. 197, 203
Banse, B.A. 202
Baragiola, R.A. 201, 202
Barbeau, C. 296
Barrett, R.C. 269
Bartel, E. 195, 197
Bassous, E. 392
Bauer, E. 191, 197, 198
Behm, R.J. 202
Beigang, R. 193
Beljakov, Yu.I 198
Bell, B. 200
Beltran, C. 52
Benbow, R.L. 192
Benedetto, J.M. 391
Benndorf, C. 197, 198, 199, 203
Bennemann, K.H. 200
Bennet, S.L. 196
Benninghoven, A. 298
Bérard, D.R. 270
Berg, J. 269
Berglund, C.N. 389, 391, 392
Berkshi, M. 193
Bermudez, V.M. 191, 193, 196
Bernatskii, D.P. 189
Bernett, M.K. 298
Bernheim, M. 194
Berry, D. 270
Bertel, E. 195, 197, 203
Bertrand, L. 298
Bertrand, P. 297, 299
Besocke, K. 200
Bibyk, S.B. 394
Bischoff, R. 297
Blakely, J.M. 197
Bleys, G. 271
Bliznakov, G.M. 202
Block, J.H. 196, 201
Blom, C.E. 269, 270
Bobrov, P.V. 390
Boer. K.W. 391

Boering, D.L. 195
Boesh, H.E. 391
Bomben, K.D. 299
Bommanavar, A.S. 193, 194
Bordeleau, A. 298
Bowman, D.R. 192
Bozack, M.J. 195
Bozso, F. 193, 195, 197, 202, 203
Bradshaw, A.M. 198
Brady, J. 271
Brand, E.S. 296
Branunig, D. 393
Brashears, S.S. 391
Brenig, W. 199, 200, 201
Brews, J.R. 394
Brezina, M. 54
Briggs, D. 297
Briggs, J. 270
Bright, R. 392
Brookes, N.B. 196
Brown, G.A. 393
Brown, P. 197
Brown, W.D. 392
Brox, M. 390
Brujin, M.P. 197
Bube, R.H. 390
Buchanan, D.A. 394
Bucksbaum, P. 193
Buntin, S.A. 201
Bunton, C.A. 270
Burmistrova, O.P. 193, 194, 195, 198, 200
Burnett, J.W. 296
Burns, A.R. 193, 201, 202
Butler, S.R. 389, 390, 391
Butz, B. 200
Byron, S. 269

Cabos, C. 271
Cadman, P. 299
Calaway, W.F. 296
Caletti, F. 194
Calise, J. 392
Campisi, G. 393
Cardon, F. 390
Carlson, Th.A. 191
Carnahan, N.F. 271
Cartier, E. 393
Casale, A. 299
Cassuto, A. 0, 199
Caudano, R. 298
Cavanagh, R.R. 201
Chaban, E.E. 192
Chaintreau, M. 194
Chan, D.Y.C. 268, 269
Chang, C.-A. 297, 299
Chang, S.T. 392
Chang, T.-C. 297
Chapmann, D.L. 268
Chaudhury, M.K. 299
Chelikowsky, J.R. 393
Chen, C.-H. 394
Chen, C.F. 394
Chen, I.D. 390
Chen, N.X. 394
Chen, S. 271
Chen, S.H. 271
Chen, Y.L. 269, 271
Chen, Y.L.E. 269
Cherry, B.W. 296
Cherry, D.W. 193
Chew, H. 393
Cho, D.L. 269
Choyke, W.J. 195, 203
Christenson, H. 271
Christenson, H.K. 268, 269, 270, 271
Christenson, J.H.K. 268
Christie, A.B. 297
Christman, S.B. 192
Chu, T.L. 390
Chu, W.-K. 298
Chuikov, B.A. 193
Churaev, N. 270
Churaev, N.V. 268
Cirlin, E.H. 298
Ciszewiski, A. 201
Claesson, P.M. 268, 269, 270, 271
Clampitt, R. 193
Clark, C.W. 196, 201
Clark, D.T. 296
Clarke, D.R. 269
Clarkson, M.T. 269
Claude, R. 296
Clinton, W.L. 199, 200
Cloutier, P. 197
Coburn, J.W. 196
Cohen, M.H. 200
Colavita, E. 193
Cole, R.K. 193
Collins, W.S. 194
Coltrin, M.E. 202
Comrie, C.M. 196
Coon, S.R. 296
Cooper, C.B. 296
Corallo, G.R. 202
Cormia, R.D. 297
Coulman, D. 196
Craig, J.H. 192, 202
Craig, J.H., Jr. 194, 198
Crine, J.P. 298
Cristoloveanu, S. 394
Cunnane, V.J. 52
Czyzewski, J.J. 192, 198, 202, 203

Dai, L. 299
Danchenko, V. 391
Daniels, R.R. 193
Datziev, M.I. 198
Davis, E.A. 392
Dawson, P.H. 189, 198, 202
de Nijs, J.M.M. 390
de Segovia, J.L. 202
de Visschere, P. 394
Debever, J.M. 194
Degras, D.A. 194
DeKeersmaecker, R.F. 389, 391, 392
Delchar, T.A. 190
Delord, J. 271
Demen'tev, A.P. 191
Demster, A. 189
Demuth, J. 297
Denber, M.L. 198
Dennebouy, R. 194
Derbenwick, G.F. 392
Derjaguin, B.V. 268, 269
Desorbtsiya, Lazwenaya 189
Dessai, V.D. 391
Dettre, R.H. 298
DiMaria, D.J. 389, 391, 392, 393, 394
DiStefano, T.H. 390, 391, 392
Dobretsov, L.N. 190
Doering, D.L. 200, 203
Doerries, E.M. 190
Domingue, A. 298, 299
Donaldson, E.E. 191
Donelson, J.J. 192
Dong, W.D. 193
Dorshow, R. 270
Dosselmann, J. 196, 201
Drachsel, W. 196, 201
Dresser, M.E. 203
Dresser, M.J. 193, 195, 199, 200
Drinkwine, M.J. 196
Dubchak, A.P. 393
Dubinina, E.M. 191
Ducker, W. 268
Dunlap, B.I. 201
Dupeyrat, M. 52
Dussel, G.A. 391
Duszak, M. 394
Dwight, D.W. 297
Dylla, H.F. 202
Dynes, P.J. 298
Dzhalilov, S.T. 191, 192, 194, 195, 198
Dzyaloshinsskii, I.E. 268

Eastman, D.E. 192, 199, 390
Eccleston, W. 391, 393
Eckstein, W. 296
Egitto, F.D. 297
Eisenthal, K.B. 268
Eitan, B. 393
Ekwelundu, E.C. 195, 196
Elango, M.A. 190
El-Dessouky, A. 390
Emin, D. 201
Engel, T. 197
Engelhardt, H.A. 192
Enk, R.C. 392
Eriksson, J.C. 270
Ernst, M.-L. 197
Ertl, G. 202, 297
Esrick, M. 200
Esumi, K. 299
Evans, D.F. 268, 269, 271
Evans, J.F. 191
Evans, R. 270
Ezaki, S. 53

Fahrner, W.R. 393
Faigon, A. 390
Falco, C.M. 296
Falicov, L.M. 200
Fang, J. 270
Fedorov, G.G. 192
Fedorov, V.I. 393
Fedorus, A.G. 191
Fedotowsky, A. 394
Feibelman, P.J. 191, 195, 201
Feigl, F.J. 389, 390, 391, 393
Feinerman, A. 298
Feldhaus, J. 197
Feldman, L.C. 193
Ferreira, C.M. 296
Ferrell, H.H. 192
Fessehaie, M. 299
Fetters, L.J. 269
Feulner, P. 192, 193, 194, 195, 199, 200, 201
Finney, L.S. 297
Fischetti, M.V. 393, 394
Fisher, G.E. 189, 196
Fitting, H.J. 391
Fleetwood, D.M. 394
Flodstrom, A. 196
Flodstrom, S.A. 192, 196, 197
Floyd, G.R. 194
Foley, H.E. 199
Fontanella, J.J. 296
Forcada, M.L. 270
Ford, R.A. 296
Fowler, R.H. 392
Franchy, R. 196
Frangopol, P.T. 53
Frank, C. 271
Frednenberg, A. 192
Freed, K.F. 200
Freedman, J.F. 295

Friemann, J.V. 391
Frodstrom, S.A. 195
Frohman-Bentchkowsky, D. 391, 393
Frost, D.C. 299
Fujimoto, H. 297
Fujimoto, T. 54
Fujiwara, Y. 53
Fukunaga, K. 53
Fuller, N. 268
Fuller, N.L. 271
Furukawa, T. 53

Gadijak, G.V. 394
Gadzuk, J.W. 196, 200, 201
Gale, R. 393
Gallon, T.E. 194
Galperin, Ye.L. 296
Garcia, A.A. 268
Gardella, J.A. 298
Garrison, B.J. 199
Geblewicz, G. 52
Gee, M.L. 269
Geil, P.H. 296
Gengenbach, T.H. 299
Georges, J.M. 270
Gerritsen, H.C. 197
Gersten, J.T. 199
Ghosh, A.P. 194
Ghosh, P.K. 297
Gibbs, R.A. 199
Gillen, G. 194
Girault, H.H.J. 52
Giszevski, A. 196
Goetzberger, A. 392
Goltviannski, Y.V. 393
Golub, M.A. 297
Gomer, R. 191, 192, 195, 197, 200, 202
Gomoyunova, M.V. 190
Gomsa, G. 202
Gonchar, V.V. 191
Gondair, K. 54
Good, R.J. 299
Goodman, A.M. 392
Gordon, A.J. 296
Gorodetskii, D.A. 197
Gortel, Z.W. 192, 200, 201
Gossedge, G.M. 299
Gotoh, T. 191
Goudeau, H. 52
Gouy, M. 268
Granick, S. 270
Grant, J.T. 193
Grant, W.A. 298
Green, T.A. 202
Greenwood, C.L. 196
Gregg, S.J. 270
Grégoire, Ch. 298
Griesser, H.J. 299
Grove, A.S. 390
Gruen, D.M. 194, 202, 296
Gruen, D.W.R. 271
Gu, S-W. 200
Gubanov, A.I. 194, 195
Gubbins, K.E. 270
Gujrathi, S.C. 298
Guo, X. 196, 201
Gupta, H.M. 391
Gutmann, R.J. 295
Guzonas, D.A. 270

Haas, C. 300
Haase, J. 197
Haglund, R. 189
Haglund, R.F. 193
Haglund, R.T., Jr. 193
Hagstrum, H.D. 199
Hall, S. 393
Haller, W. 269
Halsted, J.B. 195
Hamann, D.R. 190
Handerson, M.A. 199
Haniers, R.I. 202
Hanrahan, C. 198
Hansevarov, R.Yu. 393
Hanson, D.M. 192, 197, 198
Harker, A.H. 201
Hart, R.G. 296
Hartman, T.E. 189
Hartstein, A. 389, 392
Hashimoto, M. 53
Hata, T. 296
Hayashi, K. 53, 54
Hayashi, Y. 393
Hayes, T.R. 191
Head-Gordon, M. 203
Heiman, P.J. 192
Heller, E.J. 201
Helm, C.A. 269
Henderson, M.A. 198, 203
Hercules, D.M. 298
Herder, P.C. 269, 270, 271
Hertz, H. 269
Heyns, M.M. 391, 392
Hien, N.C. 192
Hien, N.V. 194
Hieu, N.V. 202
Higginbotham, I.G. 194
Himpsel, F.J. 192
Hirayama, M. 299
Hloder, G.A. 190
Hobson, J.P. 189
Hock, J.L. 191, 192, 194
Hoffbauer, M.A. 193, 196
Hoffman, A. 196, 201
Hoffman, F.M. 198
Hoflund, G.B. 202

Hogue, J.V. 193
Holland, S. 390
Holland, S.P. 199
Homolka, D. 54
Honig, R.E. 296
Hooker, M.P. 193
Horiuti, J. 190
Horn, R.G. 269, 270, 271
Houston, J.E. 198
Houston, J.S. 196
Hovland, C.T. 202
Hu, C. 390
Huanf, J.S. 271
Huang, J.-L. 297
Huang, L.M. 52
Hubbard, J. 201
Hubner, W. 200
Hudson, J.B. 193
Hughes, B.D. 269
Hughes, H.L. 393
Hughes, R.C. 390, 391
Hughes, W.T. 189
Huheey, J.E. 297
Huric, Z. 193
Hurich, Z.H. 192
Hurych, Z. 194, 198
Hussain, Z. 197, 201
Huston, F.L. 196
Hutson, F.L. 201

Ichimiya, A. 191, 195
Ichinose, H. 53
Ignatiev, A. 195, 196
Iiyama, S. 53, 54
Iko, K. 53
Imamura, A. 297
Iniewski, K. 394
Inokuchi, H. 297
Ionov, N.I. 189, 191, 192, 195, 197
Iordache, O. 53
Irene, E.A. 392
Irimajiri, A. 53
Iriyama, K. 53, 54
Ischuk, V.A. 191
Ishii, T. 53, 54
Ishikawa, Y. 189, 199
Ishitani, A. 299
Israelachvili, J. 271
Israelachvili, J.N. 268, 269, 270
Itoch, N. 201
Ivanov, A.S. 54
Ivantsov, L.F. 194

Jaeger, R. 192, 196, 197
Jaenicke, S. 196, 201
Janow, R. 199
Jansson, J.-F. 299
Jelend, W. 194, 198
Jennison, D.R. 193, 194, 201, 202
Johannsen, T. 390
Johnson, A.L. 194, 196, 198, 199, 203
Johnson, A.Z. 199
Johnson, J.F. 299
Johnson, K.L. 269
Johnson, P.D. 192
Johnson, R.E. 298
Johnson, W.C. 391
Jones, J.O. 191
Jones, P.L. 202
Jones, V.O. 195
Joos, P. 271
Joyce, B.A. 196
Joyce, S.A. 194, 196, 198, 199
Jutila, R.E. 200

Kaelble, D.H. 298
Kagaku, Bunseki 52, 53
Kaifu, K. 53
Kaizuka, H. 269
Kakiuchi, T. 52
Kaloyeros, A.E. 295
Kamaya, H. 53
Kambara, T. 54
Kamo, N. 53
Kamocsai, R.L. 391
Kanash, O.V. 191
Kanzaki, H. 192
Kaplan, R. 191
Kapoor, V.J. 389, 394
Kapustinskii, A.F. 54
Kartashov, A.S. 390
Karvaly, B. 54
Kasabov, S.G. 198
Kasai, H. 200
Kato, M. 53
Kato, S. 270
Kawaguchi, Y. 191
Kawai, R. 199, 200
Kawakami, H. 53
Kawakubo, T. 53
Kawamura, K. 53
Kawasaki, K. 194
Kékicheff, P. 270, 271
Kelber, J.A. 193, 202
Kendall, B.R.F. 189
Kendall, K. 269
Kendelewicz, T. 196
Kervin, R.E. 190
Kesmodel, L.L. 200
Kihara, S. 52, 54
Kim, J.T. 53
Kim, Y.-K. 297
Kim, Y.Y. 389
King, D.A. 193, 198

King, D.S. 201
King, J.G. 202
Kioka, T. 194
Kirst, T.R. 194
Kiskinova, M. 197, 199
Kiskinova, M.P. 202
Kitazaki, Y. 296
Kitchener, J.A. 270
Kiv, A.E. 190
Kjellander, K. 268
Klauber, C. 198, 203
Klemberg-Sapieha, J.E. 297
Kliem, H. 390
Klimenko, E.V. 191
Klinger, M.I. 190
Klopfer, A. 192, 195
Knights, J.C. 392
Knoll, M. 393
Knotek, M.L. 191, 194, 195, 196, 197, 201, 202
Kobatake, Y. 53
Koel, B.E. 202
Kolasinski, K.W. 195, 203
Kornelsen, E.V. 189
Kortov, V.S. 189
Koryta, J. 52, 54
Koshcheev, A.P. 196
Koster, H. 391
Kotani, M. 191
Kotlarchyk, M. 271
Kott, S.J. 269
Koyano, T. 53
Krahl-Urban, B. 192, 200
Kraus, J.S. 193, 194, 198
Kreiger, G. 393
Kremer, M. 198
Kreuzer, H.J. 192, 200
Kruchinin, A.A. 390
Ksabov, S.G. 197, 199
Kubiak, C.D. 202
Kuleshov, V.F. 191
Kumazawa, N. 54
Kunitake, T. 54, 270
Kunz, C. 196
Küppers, J. 297
Kurihara, K. 270
Kuroda, Y. 53, 54
Kurtz, R. 197
Kurtz, R.L. 195, 196, 197, 199
Kusu, F. 53
Kutsenko, E.N. 191, 192, 197
Kuznetsov, Yu.A. 190, 193, 194, 196, 198

Laflere, W.H. 390
Lai, S.K. 392
Lakshmanna, V. 391
Lam, Y.W. 393
Lama, F. 189
Lambert, R.M. 196
Lamontagne, B. 297, 299, 300
Lampert, M. 390
Landau, L.D. 268
Lanford, W.A. 295
Lang, N.D. 199, 200
Lanzillotto, A.-M. 197, 199, 201, 202, 203
Larsson, C.U.S. 196
Larter, R. 52, 53
Laskowski, J. 270
Lasneva, E.F. 189
Laux, S.E. 394
Lecante, J. 194
Leck, J.H. 191
Leclerc, G. 299
Lee, C.H. 390
Lee, L.-H. 298
Legler, W. 198
Lehovec, K. 394
Lelis, A.J. 391
Lenahan, P.M. 389
Léonard, D. 297
Levy, S.B. 295
Lewis, J.E. 392
Lhoest, J.B. 299
Li, Y.Q. 268
Liaw, C.-F. 297
Lichtman, D. 191, 192, 194, 196, 202
Liebel, G. 297
Liebl, H. 192
Lifshitz, E.M. 268
Lin, J.C. 192, 195, 202
Lin, K.C. 299
Lindsay, S.M. 268
Lipatov, Yu. 298
Liston, E.M. 296
Ljunggren, S. 270
Lopasta, E.S. 297
Lopez Sancho, J.M. 192, 199, 201
Lopez Sancho, M.P. 192, 199, 201
Losch, W. 194
Loubet, J.L. 270
Loubriel, G. 193, 196, 201
Loubriel, G.M. 202
Love, P.J. 196
Lushchik, A.Ch. 203
Lushchik, Ch.B. 190, 203
Lyon, S.A. 391, 392

Ma, T.P. 393
Mack, J.U. 203
Mack, R.A. 189, 196
Madden, H.H. 194

Madey, T.E. 189, 190, 191, 192, 194, 195, 196, 197, 198, 199, 200, 201, 202, 203
Madhuker, A. 200
Maeda, K. 52, 54
Maeda, S. 53
Magee, C.W. 393
Magomedov, A. 200
Magomedov, A.M. 194, 195, 198
Makino, M. 53
Mara, J. 269
Marcelja, S. 268
Marecec, V. 52, 54
Margaritondo, G. 193, 194, 198
Margot, J. 296
Marinova, Ts.S. 197
Mark, P. 390
Marmet, P. 189
Martin, R. 198
Martinez, J.M. 193
Martinu, L. 296, 297, 299, 300
Maserjian, J. 392, 393
Mashovetz, T.V. 190
Massoud, H. 392
Mater, J. 299
Matheson, R.R., Jr. 296
Matienzo, L.J. 297
Matsubara, Y. 52, 53
Matsui, M. 52, 54
Matsui, Y. 53
Matsumoto, N. 53
Matsuno, T. 53
Mayer, J.W. 298
Mazara, W.P. 394
McDowell, C.A. 299
McGarrity, J.M. 391
McGovern, I.T. 197
McGrath, R. 197
McGuiggan, P.M. 268, 269, 270, 271
McGuire, E.J. 190
McKee, C.S. 191
McLean, F.B. 391
McQuistan, R.B. 191
McWhorter, P.J. 393, 394
Mechetin, A.M. 189
Mehta, D.A. 390
Mel'nik, Yu.P. 197
Mendenhall, M.H. 193, 300
Menzel, D. 190, 191, 192, 194, 195, 196, 197, 198, 199, 200, 201, 202
Metiu, H.M. 198
Meyer, K. 296
Michael, R.S. 298
Miki, H. 194
Miklavic, S. 271
Miller, C. 52
Miller, S.L. 394
Minkin, V.I. 296
Minoura, N. 53
Misawa, K. 53
Miskovic, Z. 198, 200, 203
Miskovic, Z.L. 200
Mitchell, D.J. 268
Miura, Y. 391
Miyamoto, Y. 53
Mizerov, M.N. 391
Mohammed, M.A. 299
Moisan, M. 296
Molnar, A.A. 54
Momose, Y. 299
Monchalin, J.-P. 298
Mongeau, B. 298
Monnier, A. 52
Monnier, A.M. 52
Montfort, J.P. 270
Moog, E.R. 193
Moore, G.E. 189, 191
Morad, M. 392
Moraes, A.B. de Mario 202
Mori, T. 192
Morita, S. 53
Morivaki, M.M. 393
Morizumi, T. 53
Morosoff, N. 295, 296
Morris, R.J. 193
Morrison, J.D. 189
Moskalev, A.A. 192
Mott, N.F. 391
Moulder, J.F. 299
Mueller, P. 52
Muller, T. 195, 200
Muller, V.M. 269
Muraka, S.P. 295
Murata, T. 53
Murday, J.S. 201
Murnick, D.E. 193
Murray, J.R. 394
Myasnikov, I.A. 196

Nabok, A.V. 393
Nagai, K. 393
Naito, M. 54
Nakache, E. 52
Nakamoto, T. 53
Nakashima, N. 54
Naumovets, A.G. 191
Neave, J.H. 196
Nesterenko, B.A. 190, 393
Netzer, F.P. 197, 198, 199, 200, 203
Newns, D.M. 199
Newsham, I.G. 193
Ngva, C. 393
Nicolet, M.-A. 298

Nicoll, D.F. 270
Nicollian, E.H. 389, 391, 392
Niehus, H. 191, 192, 194, 197, 203
Niehus, N. 202
Niles, D. 193
Ning, T.H. 390, 391
Ninham, B.W. 268, 269, 270, 271
Nishijima, M. 191, 196
Nissan-Cohen, Y. 391, 393
Nitta, J. 53
Nobl, C. 203
Noell, J.O. 191
Norman, D. 196, 197
Nosaka, M. 53
Novikov, S.V. 391
Nyholm, R. 195, 196

Oechsner, H. 296
Offenberg, M. 390
Ogawa, S. 390
Ogino, M. 299
Ogura, K. 52, 54
Ohta, T. 297
Ohtani, S. 191
Oinuma, S. 54
O'Kane, D.F. 295
Okazaki, S. 299
Oldham, T.R. 391
Olsson, U. 271
Omel'yanovskaya, N.M. 191
Omochi, T. 53, 54
Ong, S. 268
Ooij, W.J. 299
Opila, R. 202
Osaka, T. 52
Oshirai, O. 52
Osipov, O.A. 296
Outlow, R.A. 202
Overbeek, J.T.G. 268
Owen, I.G. 196
Owen, L.W. 196
Owens, D.K. 298
Ozaki, N. 53, 54

Padgornik, R. 270
Pai, D.M. 392
Pal, S. 200
Pan, F.-M. 297
Pan, J. 268
Pang, S. 391
Panitz, J.A. 192
Pant, H.C. 54
Pantano, C.G. 189
Pantelides, S.T. 389
Paraszczak, J. 296
Parenteau, L. 191, 195, 196, 197
Park, Ch. 198
Parker, J.L. 268, 269, 270, 271
Parks, C.C. 196, 201
Parrill, T.M. 191
Parsegian, V.A. 268, 271
Pashley, R.M. 268, 270, 271
Pavlov, V.G. 189
Payn, J.K. 191
Peatman, W.S.B. 193
Pellin, M.J. 194, 202, 296
Penka, V. 202
Pepper, S.V. 299
Perenteau, L. 202
Perez, E. 271
Peterman, L.A. 189
Petrov, P. 271
Petrov, V.V. 54
Pian, T.R. 193, 194, 198
Pickuth, A. 198
Pireaux, J.-J. 298, 299
Pitaevski, L.P. 268
Pitts, J.R. 201
Piyakis, K. 299
Plumtree, P.H. 189
Plunkett, R.J. 295
Pokrovskii, A.V. 191
Polak, M. 199
Poppa, H. 197
Porod, W. 391
Porter, R.S. 299
Potechina, N.D. 191, 197, 198
Powell, R.J. 391, 392
Predvoditelev, D.A. 54
Preuss, E. 199
Pribac, F. 269
Prince, R.H. 194
Propst, F.M. 196
Propst, F.P. 191
Prutton, M. 194
Przewlocki, H.M. 394
Ptushinskii, Yu.G. 193
Pushmann, A. 195, 196, 200
Putey, G.N. 270

Qingde, Z. 53
Quate, C.F. 269
Qui, Y. 300
Quinn, F.M. 196

Rabinovich, Y.I. 268, 269, 270
Rakhovskay, O.V. 191
Ramaker, D.E. 193, 194, 195, 196, 197, 201, 202
Ramsier, R.D. 190
Rand, P. 271
Rand, R.P. 268, 271
Rao, D. Krishna 391
Rashba, E.I. 200
Ravner, H. 298
Reber, R.A. 394

Rebuffel-Reynier, A.M. 52
Redhead, P.A. 189, 191
Refolio, M.C. 199, 201
Rehn, V. 191, 195, 196
Reilley, C.N. 296
Reisman, A. 390, 392
Revesz, A.G. 393
Rey, S. 198, 202
Ricco, A.J. 299
Rice, D.W. 295
Richardarson, C.H. 196
Richards, P.M. 202
Richetti, P. 271
Richter, L.J. 201
Riedel, R. 193
Riedl, W. 192, 194, 198, 199, 201, 202
Riggs, W.M. 297
Riley, M.E. 202
Rivière, J.C. 297
Rivkin, S.M. 190
Roberts, A.D. 269
Roberts, M.W. 191
Roberts, R.F. 297, 299
Robins, J.L. 189
Rogers, J.W. 202
Rogov, V.V. 189
Roman, E. 198, 202
Rose, A. 389
Rosenberg, B. 54
Rosenberg, R.A. 194, 195, 196, 197, 201, 202
Rosencwaig, A. 298
Rossbach, V. 299
Rousset, G. 298
Rowe, J.E. 192
Rubio, J. 192, 199, 201
Rubloff, G.W. 392
Ruckenstein, E. 270
Rüdenauer, F.G. 298
Rudge, M.R.H. 190
Rudin, D.O. 52
Ruf, H. 200
Rupp, H. 300
Russel, H. 394
Rut'kov, E.V. 191
Rutland, M.W. 271
Ryan, F.W. 299
Rye, R. 299
Ryu, K. 53

Sá, A.B. 296
Sacher, E. 295, 296, 297, 298, 299
Sacks, W. 200
Sacks, W.S. 200
Sah, C.T. 391, 394
Saida, Y. 53
Saito, M. 53
Saito, T. 296
Sakabe, K. Ota, T.53, 53
Sakaguchi, H. 53
Sakmann, B. 52
Saloman, E.B. 192
Sambe, H. 193, 195, 196, 202
Samec, Z. 52, 54
Sanche, L. 191, 195, 196, 197, 202
Sandstrom, D.R. 191, 193
Sanin, R.V. 393
Sarman, S. 271
Sass, J.K. 203
Saukiassian, P. 194
Sauvé, G. 296
Sawada, Y. 54
Sawatzky, G.A. 300
Schainkman, M.K. 190
Schiffrin, D.J. 52
Schluter, M. 393
Schmidt, M. 391
Schmidt, P.F. 389
Schmidt, R. 390
Schmidt-May, J. 196
Schmitz, W. 392
Schonhorn, H. 297
Schork, R. 394
Schottky, W. 392
Schreiber, H.P. 297
Schrott, A.G. 297, 299
Schuck, P. 200
Schuller, I.K. 296
Schwalke, U. 202
Schwartz, A.M. 299
Schweitzer, E.L. 194
Schwerin, A.V. 390, 392
Scoggan, G.A. 393
Seabury, C.W. 198
Seach, M.P. 190
Segovia, J.L. 198
Seki, K. 297
Sekigawa, T. 393
Self, F. 196
Selmani, A. 297, 299, 300
Semancik, S. 203
Senda, M. 52
Senden, T. 268
Sent, F. 195
Sessler, G.M. 299
Sexton, B.A. 297
Sha, S. 53
Shamir, N. 202
Shanfield, Z. 393
Shapira, Y. 192
Shappir, J. 390, 391, 393
Shashoua, V.E. 52
Shchukin, E.D. 270
Shelepin, N.A. 393
Sherman, E.Ya. 200

Shi, M.-K. 297, 299, 300
Shi, Y.J. 392
Shigeta, Y. 191
Shimaya, M. 390
Shimoide, K. 53
Shimooka, T. 54
Shinn, N.D. 198, 203
Shiono, N. 390
Shirai, O. 54
Shirley, D.A. 196, 201
Shirshov, Yu.M. 393
Shmartzev, Yu.V. 393
Shockley, W. 190
Shoji, M. 53
Shonhorn, H. 299
Shousha, A.H.M. 394
Shul'man, A.R. 190
Shuttleworth, D. 296
Siegel, G.J. 52
Simons, M. 393
Sing, K.S.W. 270
Sinitza, S.P. 394
Slesarev, A.I. 189
Slodzian, G. 194
Smith, D.T. 269
Smith, L.P. 189
Smith, N.V. 192
Smoluchowski, R. 200
Snitko, O.V. 190
Sobol, P.E. 299
Sokolov, N.S. 391
Solomon, T. 52
Spangler, R.A. 52
Spicer, W.E. 190
Spiegel, D.R. 296
Sroubek, Z. 190
Starkweather, H.W., Jr. 296
Starling, K.F. 271
Stasiak, J.W. 391
Stechel, E.B. 193, 197, 201, 202
Steinruck, H.P. 196
Stichle, W.F. 299
Stillwagon,L.E. 190
Stimpson, B.P. 191
Stivers, A.R. 391
Stockbauer, R. 192, 195, 196, 197, 198, 199
Stoffel, N.G. 193, 194, 198
Stohr, J. 196, 197
Stoneham, A.M. 201
Stori, M. 197
Stulen, R.H. 191, 193, 195, 202
Stuve, E.M. 203
Suezaki, Y. 53
Suga, S. 54
Sugai, S. 194
Sugawara, K. 54
Sugita, T. 53
Sugiyama, M. 54
Suib, S.L. 299
Sun, H. 200
Sun, J.Y.-C. 391
Sun, J.Y. 394
Sun, P. 54
Surdaram, V.S. 202
Suzuki, H. 53
Suzuki, M. 52, 54
Svensson, C. 389
Svirschevsky, S. 53
Swansson, R.M. 393
Szabo, A. 197, 199, 203
Sze, S.M. 390
Szedon, J.R. 390

Tabor, D. 268
Taglauer, E. 193
Takagi, S. 191
Takahashi, M. 198
Takamura, K. 53
Takano, A. 198
Takauchi, K. 198
Takeda, E. 390
Takutaka, H. 194
Tamm, I.E. 190
Tamura, Y. 299
Tan, B.J. 299
Tanaka, H. 297
Tanford, C. 270
Tao, N.J. 268
Tarantov, Yu.A. 390
Taylor, P.A. 195, 203
Taylor, S. 391
Tazawa, Y. 191
Tekhn, Pis'ma v Zh. 195, 196, 198
Tekhn, Zh. 189, 194, 198
Teorell, T. 52
Terada, T. 54
Terenin, A.N. 189
Terselius, B. 299
Teshima, R. 200
Thewes, R. 390
Thiel, P.A. 198, 202
Thiry, P.A. 297, 298
Thodin, T.N. 198
Thompson, L.F. 190
Thornton, G. 196, 197
Ti Tien, H. 54
Tkachuk, M.N. 195
Toko, K. 53, 54
Tolk, N. 189
Tolk, N.H. 193, 194, 198
Tombrello, T.A. 300
Tominaga, C. 191
Tonck, A. 270
Tongegode, A.Ya. 191
Townsend, P.D. 189

Toya, T. 190
Tracy, J.C. 197
Traum, M.M. 192, 193, 194, 198
Travkov, I.V. 394
Treicher, R. 192, 201
Tsao, Y. 269, 271
Tsukada, M. 200
Tsukiji, M. 53
Tsvankin, D.Ya. 296
Tully, J.C. 193
Turmashev, E. 191
Tuzi, Y. 193
Tzoar, N. 199
Tzou, J.J.-T. 391
Tzu, J. 394

Ueba, H. 200
Ueba, K. 198
Ueda, I. 53
Uhlaner, C.J. 198
Umbach, E. 201
Umetani, S. 54
Unguris, J. 193
Urabe, K. 53
Uram, K.J. 199
Ustinov. Yu.K. 195

Van Alsten, J. 270
van der Laan, G. 300
van der Schoot, J.J. 394
Van der Veen, J.F. 192, 199
Van der Weil, M.J. 197
van Hunsel, J. 271
van Meirhaeghe, R.L. 390
van Ooij, W.J. 298
van Oostrom, A. 189
van Oss, C.J. 299
van Overstraeten, R.J. 391
Vanysek, P. 54
Varley, J.H.O. 203
Vengurlecar, A.S. 391
Verhoeven, J. 197
Vermeersch, M. 298
Verwey, E.J.W. 268
Verwey, J.F. 391
Vickerman, J.C. 298
Vilar, M. Rei 298
Vlasov, Yu.G. 390
Vogel, S.L. 297
Vol'kenshatain, F.F. 190
von Hippel, A.R. 295
Voss, J. 196
Vreeland, T. 300
Vukanic, J. 198, 200, 203
Vukanic, J.V. 200
Vul,' A.Ya 393

Wagner, H. 200
Wainwright, S.P. 393
Walczak, M.M. 198, 199, 203
Walkup, R. 193
Walkup, R.E. 194, 195, 200, 201
Wallace, P.M. 203
Walters, M. 390
Wan, C.R. 197
Warburton, D.R. 196, 197
Watson, W.F. 299
Webb, M.B. 193
Weber, J. 52, 54
Weber, W. 390, 392
Weeks, S.P. 192
Weigmann, U. 201
Weinberg, Z.A. 392, 393
Wendt, R.C. 298
Weng, S.L. 202
Wennerström, H. 268, 269, 271
Werner, B.T. 300
Werner, H.W. 298
Wertheimer, M.R. 296, 297, 299
Weser, U. 300
West, J.E. 299
Westra, C. 300
Wheeler, D.R. 299
White, C.T. 201
White, D.M. 296
White, L.R. 268, 269
Whitten, J.E. 202
Wierzbicki, A. 201
Williams, B.G. 297
Williams, E.M. 191, 196
Williams, J.S. 298
Williams, P. 194
Williams, R. 392, 393
Williams, R.T. 202
Winograd, S.P. 199
Winokur, P.S. 393
Wintergall, M.C. 296
Winterton, R.H.S. 268
Wolters, D.R. 394
Woodruff, D.P. 192
Woodruff, D.R. 190
Woods, M.H. 393
Wu, C.Y. 394
Wurth, W. 196, 201
Wydeven, T. 297

Xiang, L.Z. 194
Xiaolin, Z. 268
Xie, X. 299
Xu, Z. 271

Yagusawa, K. 54
Yakshinskii, B.V. 190, 193, 194, 195, 198, 200
Yamafuji, K. 53, 54
Yamamoto, H. 297
Yambe, K. 391
Yaminsky, V. 271

Yaminsky, V.V. 270
Yang, S.X. 269
Yarmoff, J.A. 196
Yasuda, H. 295, 296
Yasue, E. 191
Yasue, T. 195
Yates, J.T. 190, 191, 193
Yates, J.T., Jr. 190, 191, 192, 195, 196, 197, 198, 200, 201, 202, 203
Yelon, A. 297
Yokoi, S, 54
Yong, J.R. 189
Yoon, R.H. 270
Yoshida, M. 5, 53
Yoshida, T. 54
Yoshida, Y. 54
Yoshida, Z. 52, 54
Yoshikawa, H. 194
Yoshikawa, K. 52, 53, 54
Yoshioka, T. 53
Young, C.E. 194, 202
Young, D.R. 389, 390, 392
Yousif, M. 193
Yu, H.N. 390
Yu, M.L. 191, 197
Yun, B.H. 390, 394
Yuschenko, V.S. 269, 270

Zamani, N. 393
Zana, R.J. 270
Zandberg, E.Ya. 189, 191
Zaporohenko, V.I. 191
Zartner, A. 192
Zavadil, J. 190
Zdansky, K. 190
Zegers-van Duynhoven, A.T.A. 394
Zettlemoyer, A.C. 299
Zhang, J.F. 391
Zhang, Q.-J. 192, 202
Zhang, Q.I. 194
Zhdanov, Yu.A. 296
Zimmerer, G. 194
Zingerman, Ya.P. 191

SUBJECT INDEX

Adparticle
  bond orientation re: surface 179–187
  DIET cross-section vs. concentration 112–117
  interactions 186–187
  localization 176–178
Adsorbate dissolution kinetics
  DIET-based study 172–173
Adsorption
  adparticle interactions 69–70
  chemisorption 66–68
  particle migration in 68–69
  particle-surface system in 67–68
  physical vs. chemical 66–67
  physisorption 68
Adsorption states of surface particles 173-176
  angular distribution of ESD ions in 174
  catalytic heterogeneous reactions 175–176
  transition from physi- to chemisorbed state 175–176
Adsorption-desorption
  CO/Pt(iii) 181–182, 185–186
  ESDIAD study 182–185
  H/Ni(111) 185, 186
  H_2O/Ru(100) 182, 184–185
  NH_3/Ni(110) 183–184, 186
  PF_3/Ni(111) 184–185
Adsorption-desorption kinetics
  DIET-based study 171–172
Air-vapor interactions, surfactant monolayer/solid surface
  adhesion 233–235
  hysteresis in 235, 243
  layer thickness 232–233
Angular distribution of ions in ESD 81–84, 170–171, 174. *See also* Electron-stimulated desorption ion angular distribution (ESDIAD)
(Angular distribution...) in PSD 84–85. *See also* Photo-stimulated desorption ion angular distribution (PSDIAD)
Antoniewicz model of single-electron excitations
  ESD of neutrals 146–148
  ESD of positive ions 150
  potential energy of metal-adsorbate system 147
  quantum-mechanical study of 151
    ESD from physisorbed layers 151–152
    neutral ESD from physisorbed state 152–154
  verification of 150–151
AOT water in oil emulsion/mica interaction 261–266
  micellar system 265–266
    reversed 261–264
Aqueous/organic interfaces
  electron transfer at 31–34
  ion transfer at 23–24
    ionophore and surfactant facilitation 28–31
  oscillating systems
    anionic surfactants in 9–10
    cationic surfactants in 6, 8–9
    without surfactants 10–11
  oscillations at 7
Auger processes
  in desorption 155–158
  in recombination of holes and electrons 64–65

Bilayer lipid membranes
  ion transfer through 37–39
  oscillations at 16–20
Bimorph surface force apparatus
  adhesion measurements 229–232
  advantages of 215

(Bimorph surface force)
diagrams of 214, 218, 219
estimation local radius of curvature 228–229, 230
experimental setup 219
interferometric FECO 219–220, 222, 224, 228
operation and data collection 220–221, 222, 223
optical setup 219–220
problems with 214–216
surface deformations 22, 224–228

Cationic surfactant solusolutions/surface interactions
double-chained
DHDAA 259–261
OA and DA 258–259
single-chained surfactants 254–259
CTAB 254–259
DDOABr 238–240, 259, 260
Cavitation
fluorocarbon-coated mica 249
mechanisms in hydrophobic interactions 252–254
Cetyltrimethylammonium ammonium
bromide (CTAB). *See* CTAB (cetyltrimethylammonium bromide)
Charge carrier transport 371, 385–387
versus first-order trapping 387
space-charge limited current 386–387
steady-state current 385–386
total time 386
Charge carrier trapping
centers and charge kinetics 328
coupling effects
Coulomb screening of traps 379–385
near injecting interface 376–379
strong 371–376. *See also* Strong coupling effects
first-order kinetics
distortion of 311–315, 377–378
electron 314–315, 322, 324
hole 315, 322, 323, 324

(Charge ... kinetics)
multiple-trap model 313–315
single trap model 311–313
injection-limited current mode 308–311
recombination effects 324–326
carrier trapping kinetics 325–326
space charge-limited current 308–310
trap generation
during injection 326–328
kinetics of 327–328
Charge carriers
detrapping from trapping site 316–324
bulk insulator 316–321
charge density in 316–318
effect on charge accumulation kinetics 323
electron transitions 316, 317
hopping to neighbor defect 317, 320–321
impact ionization 317, 319–320
photo-depopulation 318, 319, 365, 366
thermal 318–319, 365
thin insulators 321–324
tunneling 317, 319, 321–323
monopolar photoinjection of 337–340
negative and positive biases 365–366
neutralization of opposite sign 364–365
thermal and field stimulation 332–337
avalanche carrier injection 332–334, 335
avalanche electron stimulation 334, 336, 337
avalanche hole stimulation 336
Charge trapping defects
in MIS structures 304–305
in SI structures 304
Chemisorption
gas 66–67
vs. physisorption 66–67
Contact potential difference (CPD)
patches with different work functions 73–75

(Contact potential, cont.)
patches with uniform and nonuniform work function 74, 75
Coulomb screening of traps 379–385
effect of 380
field dependence of cross-section for hole trapping 383
inactivated volume model 380–381, 382, 383–384
in-plane trap distribution 381–382
CTAB cationic surfactant solution
on mica surface 254–259, 260
bilayer 255–256, 257, 258, 259, 260
monolayer 232–235, 254–255, 260
on silica glass 256-257 258, 259, 260

DA. *See* Dodecylammonium (DA) chloride
DDOABr. *See* Dioctadecyl-dimethyl ammonium bromide (DDOABr)
Desorption induced by electronic transitions (DIET). *See* DIET
Desorption process, stages of 134–135
DHDAA. *See* Dihexadecyldimethyl ammonium acetate (DHDAA)
DIET
desorption described 57–58
distribution of desorbing particles. *See also* Angular distributions; Energy distributions
effect of 58
experimental technique 76–97
common features of 95–97
neutral particle detection 85–95
positive and negative ion detection 76–85
features of 98–134
dependence on incident radiation intensity 98–100
distribution of desorbing particles 122–134
isotope effect 121–122
(DIET, cont.)
mechanisms of
many-electron excitations 154–168
negative ion desorption 168–171
single-electron excitations 125–154
uses of 58–59
DIET cross-sections
versus adparticle concentration 112–117
dependence on substrate temperature 118–121
yield for ions and neutrals 100–112
DIET cross-sections and yield
binding energy of adsorption systems 101–102
dependence on substrate temperature 118–121
neutrals 120–121
O^+ ESD for O-saturated surfaces 118–119, 120
desorption threshold differences 101–102
of ions 100–102
localization of primary electron excitation 119–120
of neutrals 100, 102, 111–112
DIET cross-sections vs. adparticle concentration
concentration dependencies
ESD cross-sections 115–116
ESD neutrals 11, 116, 117
ESD ion current increase 112–113
ESD of negative ions 116–117
O^+ ESD $i^+/Mo(100)$, $W(100)$ 112–113
DIET study preparation
AES of surface cleaners 97
surface decontamination 96–97
ultrahigh vacuum installations 95-96
Dihexadecyldimethylammonium acetate (DHDAA)/mica 259–261
interaction forces 259–261
Dioctadecyldimethylammonium bromide (DDOABr)/mica interactions
divalent $MqSO_4$ 240–241

(Dioctadecyldimethylammonium)
trivalent electrolyte solutions 239–240
Dodecylammonium (DA)
chloride/mica interactions 238, 258–259, 260

Electrolyte effect on hydrophobic interaction, surfactant/surface 237–242
Electron energy spectrum
solid surface 59–61
Electron excitation
collective 62–63
electron-stimulated 61–63
energy dependence in 61–62
many 154–168. *See also* Many-electron excitations
photon-stimulated 63
recombination of holes and electrons 64–66
single 135–154. *See also* Single-electron excitations
Electron photoinjection probe charge analysis 359–364
cross-over voltage in 363
examples: photoinjection curves 359–360, 361
I-V curve distortion 364
I-V measurements of 363–364
negative fixed charge in insulator 359, 360
problems with resolution 362–363
Electron relaxation
nonequilibrium carrier 63–64
Electron transfer
at aqueous/organic interface 31–34
Electron-hole plasma generation 340–345
injection current control 342–343
irradiation technique 340–341
monopolarity of injection 343–344
vacuum ultraviolet 341–342
Electronic desorption. *See* DIET; Electron-stimulated desorption (ESD)
Electron-stimulated desorption (ESD)
of negative ions 80
(Electron-stimulated, cont.)
neutral particle detection in 85–95. *See also* Neutral particle detection in ESD
study of positive ions 76–81
cylindrical magnetic spectrometer 79–80, 81
cylindrical mirror analyzer 79, 80
retarding field analyzer 76–78
TOF mass spectrometers
Electron-stimulated desorption (ESD) cross-sections
secondary electron contribution in 106–108, 112
thresholds
for ions 110–111
for negative ions 105, 106, 107
for positive ions and neutrals 78, 79, 103–104
Electron-stimulated desorption ion angular distribution (ESDIAD) 129–134
anistrophy in 133–134
detection of 81–84
techniques 81–82
factors affecting 129–130
information from
particle bond orientation on surface 128–131
particle vibrations on surface 131–132
negative ions 133–134
neutrals 133
patterns 130, 131, 132
and PSDIAD 130–131
setup and operation 82–83
setup with displaceable electron multiplier 83–84
Energy distributions of ESD particles 122–129
ESD of alkali metal ions 123–124
of molecules 128–129
of negative ions 126
of neutrals, alkali metal atoms 126–128
of positive ions
incident electron energy dependence 124–125
surface adsorbate coverage 125–126

(Energy distributions, cont.)
surface temperature dependence 125
ESD. *See* Electron-stimulated desorption (ESD)
ESDIAD. *See* Electron-stimulated desorption ion angular distribution (ESDIAD)

FECO. *See* Fringes of equal chromatic order (FECO) interferometry
Fluoropolymer metallization 274–295
deposition mechanisms 283–284
dielectric properties of insulators 275–278
energetics of 282–283
depositing metal-polymer reaction 283
metal condensation energies 282
metal sputtering 282–283
polymer bond energies 283
fluoropolymers 278–279
microelectronics 274–275
modified surfaces 292–293
plasma techniques 284–285
surface analytical techniques 285–290
HREELS 287, 291
nuclear scattering 288
PHAS-PAS/FTIR 287, 291
SIMS 288–289
XPS 285–286, 291, 292, 293
surface modifications 294
for chemical 284–285
surface thermodynamics 279–281, 289–290, 292
theoretical support 294
unmodified surfaces 290–292
Fringes of equal chromatic order (FECO) interferometry
estimation of local radius of curvature 228–229, 230
surface deformations and 222, 224
in surface force separation measurement 219–220

Glass surface (modified)
hydrophobic surfactant interactions 246–250
(Glass surface, cont.)
surfactant interactions
$FSCl_2$-treated 246–247, 249
monochlorosilane-treated 250
results 249, 250
silinated 246

Hydrophobic interactions, surfactant monolayer/solid surface
cavitation mechanisms 252–254
electrolyte effect on 237–242
electrostatic model 251–252
fluorocarbon monolayers 236, 237
glass surface, modified 246–250
hydrocarbon surfaces 235–237
hydrophobic-hydrophilic surface 250–251
LB monolayer on mica 235–236
microviscosity measurements 242–246
structural model 251
theoretical models 251–254

Incident radiation intensity
DIET dependence on 98–100
Injection current charge monitoring 349–352
charge spatial location 351
external field current 349
field at interface 349–350
limitation of 351–352
Injection spectroscopy 301–388. *See also* Charge carrier trapping
carrier injection mechanisms 329–348
electron-hole plasma generation 340–345
monopolar photoinjection 337–340
SI interfacial carrier 329–331
thermal and field-stimulated 332–337
tunnel and impact ionization 3454–348
carrier trapping in injection-limited current mode 308–329

(Injection spectroscopy...)
charge trapping kinetics and 328–329
determination of trapping centers parameters 328–329
detrapping effects 316–324
first-order kinetics 311–315
recombination effects 324–326
space charge limited and injection limited currents 308–311
charge monitoring techniques 348–370
electron injection probe 359–364
injection current 349–352
SI field-effect 353–359
trap depopulation spectroscopy 364–370
transition to space-charge limited current 385–387
trapping coupling effects 371–385
Coulomb screening of traps 379–385
near injecting interface 376–379
strong carrier 371–376
Interferometric surface force apparatus
forces in cationic micellar solutions 254–259, 260
hydrophobic surface interactions 235–254
fluorocarbon monolayer 237
glass surface 2446–250
hydrocarbon surface 236–237
hydrophobic-hydrophilic surfaces 250–251
mica/cationic surfactant interactions 232–235
Ion transfer processes
at aqueous/organic interface electron transfer 31–34
facilitation by ionophores or surfactants 28–31
half-wave potentials of ions 23–24, 26–27
relationship with ion characteristics 24–28
voltammogram for 23–24
at immiscible electrolyte solutions interface 20–23
(Ion transfer processes...)
through a membrane
bilayer lipid 37–39
reaction influence at W2/M interface on W1/M interface 36–37
relation between membrane and aqueous/membrane interfaces 34–36
voltammogram for 34–39
at W/NB interface
polarograms for 50, 51
Ionophores in ion transfer facilitation 28–31
Ions
angular field of distribution. *See also* Electron-stimulated desorption ion angular distribution (ESDIAD)
in ESD 81–84
dependence on incident energy 163
DIET dependence on incident radiation intensity 97–98
ESD cross-section and yields 100–102
ESD of 76–81
PSD cross-section and yield 103, 105, 110–111
Isotope effect(s)
ESD of ions and neutrals 121–122, 139
ESD of positive ions 161–162

Lipid membrane(s)
bilayer
ion transfer voltammogram 37–39
oscillations at 16–20
multilayer
oscillations at 16–20
Liquid membranes
oscillating systems
anionic surfactants 9–10
cationic surfactants 6, 8–9
without surfactants 10–11
oscillations at 7
Local surface field relaxation (LSFR)
atom energy distribution 165
desorption of neutrals in 165–167
ESD with reverse motion 163
ion yield dependencies on incident energy 163

(Local surface field...)
isotope effects for positive ESD ions 161—162
PSD electron interactions 164
vs. MGR model 160—161

Many-electron excitations
auger-stimulated desorption 155—158
lattice recoil 167—171
local surface field relaxation 158—167. *See also* Local surface field relaxation (LSFR)
Membrane current or potential oscillations
membrane current under applied membrane potential 43, 48
membrane potential under applied membrane current 40—42
relation with voltametric maxima 50—51
Membrane filter oscillations
additives and 15—16
in DOPH-doped
between aqueous KCl and NaCl solutions 14—15
between two aqueous KCl solutions 12—14
in lipid-doped 11—20
at lipid-impregnated single pore 16
Membrane oscillations
at aqueous/organic interfaces or liquid membrane systems 6—11, 19
anionic surfactants and 9—10
cationic surfactants and 6, 8—9
summary 7
surfactant absence 10—11
at artificial membranes 5—20
at bilayer or multilayer lipid membranes 16—19, 20
at lipid-doped filters 11—20
DOPH between aqueous KCl solutions 12—14
DOPH between KCl and NaCL solutions 14—15
in presence of additives 15—16
at single pore, 16, 17
Membrane potential or current 39—51
oscillations
electrolytic cells for observation 39—40
voltametric elucidation 39—51
under applied membrane current 40—42 47
electrocapillarity curve at W/NB interface 45—47
ion transfer through M, W1/M, W2/M 43—45
Membrane(s). *See also* named Membrane
artificial 5—20
lipid 16—20, 37—39
liquid 6, 8—11
Menzel-Gomer-Redhead (MGR) model, single-electron excitations
adsorbate-substrate interaction 145
desorption threshold 137
electron capture 137
ESDIAD
image potential effect 141—142, 143, 144
ion neutralization 142—144
ion desorption probability 137—138
ion energy distributions 146
ion neutralization at surface 145
modification of. *See* Antoniewicz model of single-electron excitations
neutral particle desorption 138—139
potential energy of metal-adsorbate system 135—137
quantum-mechanical studies of 144—147
adiabatic approximation 144—145
temperature dependence of ESD ion yield 140—141
WKB approximation 145
Metallization, fluoropolymer 274—295. *See also* Fluoropolymer metallization
MGR. *See* Menzel-Gomer-Redhead (MGR) model

Mica surface forces, 261

Mica surfaces in surfactant solutions 261-267
261-
in AOT water oil micro-emulsion
forces between 261—266
in CTAB solution 267
MIS (metal-insulator-semiconductor)
Multilayer lipid membranes
oscillations at 16—20

Negative ion desorption mechanisms 168—171
angular distribution 170—171
bipolar dissociation 168, 169
core level excitation 169—170
dissociative attachment 169
substrate image potential 169
Neutral particle detection in ESD 85—95
cross-section for 92—94
exclusion of thermal desorption effect 94—95
with laser-assisted ionization 89—90
with laser-induced fluorescence 90—92
mass spectrometer ion sources in
beam ionization 87
impact ionization 86
radiation of excited neutrals 92, 93
radical reaction exclusion 86
with surface ionization-based detector 87—88
thermodesorption problem in 85—86
with TOF technique 88—89
vs. gas residual 86
Neutralization of electron in trapped hole profiling
applications of 370
partial 368—370
tunnel 368, 369
Neutrals
DIET and incident radiation intensity dependence 99—100
ESD cross-section and yield 100, 102, 111—112
PSD cross-section and yield 103

Ocylammonium chloride (OA)/-mica interaction 258—259

Particles
surface
adsorption states 173—176
vibrations 178-179
Photoinjection of charge carriers 337—340
advantages of 339—340
limitation of 339
semiconductor into insulator 337—338
Photo-stimulated desorption (PSD)
angular distribution of ions 84—85
detection, ellipsoidal mirror analyzer 84—85
of ions 81
photoelectron role in 108—109, 112
secondary desorption thresholds and ion yield 110—111
Photo-stimulated desorption (PSD) cross-section and yield of ions 103, 105, 110—111
of ions and neutrals 103
threshold for ions 105
Photo-stimulated ion angular desorption (PSDIAD)
ESDAID and 130—131
patterns 132—133
Piezo electric devices
force sensor 214
surface force measurements 212—213, 214
tube 212—214, 217, 218
Potential barrier
contact fields with different work functions 73—75
at metal surface 70—71
at SI surface 71—72
PSD. *See* Photo-stimulated desorption (PSD)
PSDIAD. *See* Photo-stimulated desorption ion angular distribution (PSDIAD)

Recombination of holes and electrons 64—65

SC. *See* Semiconductor
Semiconductor Industry Association (SIA) 275

(Strong coupling...)
voltage staircase technique 375–376
Surface deformations 222, 224–228
curvature effect on 225
displacement under compression 224–225, 227, 228
effect on bimorph surface force measurement 222, 224–228
interaction forces in 224–228
interaction with strong attractive minima 228
repulsive interactions 224, 226–227
Surface electronic states
chemisorption of particles 60–61
Shockley 59–60
Tam 59
Surface force apparatus (SFA). *See also* Bimorph surface force apparatus
components 211
dynamic technique 213–214
interferometric FECO 212–213
in surface separation determination 212
Surface force(s)
double layer interactions 208–210, 211
hydration 210, 211
hydrophobic 210, 211
measurement techniques 210–231
bimorph surface force apparatus in 214–231
surface apparatus in 211–214
protrusion 210, 211
solvation 210, 211
surfactant monolayers on solid surfaces 232–254. *See also* Surfactant monolayers/solid surfaces
in surfactant systems 207–268
types of 208–211
van der Waals interactions 208, 211
Surface processes
DIET techniques in 171–187
adparticle bond orientation and admolecule structure 179–187
(Surface processes...)
adparticle localization 176–178
adsorbate dissolution kinetics 172–173
adsorbed particles state 173–176
kinetics of adsorption-desorption 171–172
particle vibrations 178–179
Surfactant monolayers/solid surfaces
air-vapor interactions 232–235
concentrated surfactant solutions 261–266
dilute cationic surfactant solutions 254–261
hydrophobic interactions 235–254
mica surfaces in AOT water in oil microemulsion 261–266
surface preparation techniques 232
Surfactant systems, surface forces in 207–268
Surfactants
in oscillating systems at aqueous/organic interfaces
absence of 10–11
anionic 9–10
cationic 6, 8–9
Surfactants in ion transfer facilitation 28–31

Teflon. *See* Fluoropolymer metallization
Temperature of substrate, DIET cross-sections and 118–121. *See also* DIET cross-sections, dependence on substrate temperature
Thin insulators
charge carriers 304–305
charge trapping 305–306
trapping properties of 306
Thin layer defects
characterization 305
factors affecting 303
study techniques 303–304, 305
TOF (time-of-flight)
Trap depopulation spectroscopy 363–370
application conditions of 367–368

(Trap depopulation...)
charge neutralization in 368—370
negative and positive biases 365—366
neutralization of opposite sign 364—365
Tunnel injection 345—348
advantages of 346
impact ionization and 347—348
problems with 346—347
Tunneling injection probe 360
Voltameters
for ion transfer
through bilayer lipid membrane 37—39
through M and interfaces of W1/M and W2/M 43—45
at two aqueous/membrane interfaces 34—36

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Scientists and Engineers active in research, development, and applications of condensed matter films

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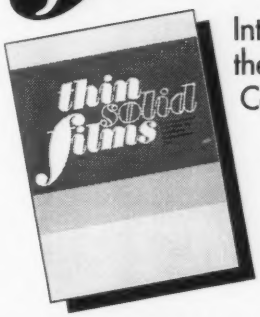

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